

#### Discrete POWER & Signal **Technologies**

# **PN3638 PN3638A**



## **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	25	V
V <sub>CBO</sub>	Collector-Base Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	4.9	V
lc	Collector Current - Continuous	800	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN3638/A	
P <sub>D</sub>	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier (continued)

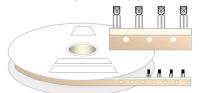
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown	$I_{C} = 10 \text{ mA}, I_{B} = 0$	25		V
* (BR)CEO	Voltage*	10 - 10 mm t, 1 <sub>B</sub> - 0			,
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage*	$I_C = 100 \mu\text{A},  I_B = 0$	25		V
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	25		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0	4.0		V
Ices	Collector-Cutoff Current	V <sub>CE</sub> = 15 V, I <sub>E</sub> = 0		35	nA
		$V_{CE} = 15 \text{ V}, I_{E} = 0, T_{A} = 65^{\circ}\text{C}$		2.0	μA
ON CHAR	RACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$			
		PN3638 PN3638A	30 100		
		$V_{CE} = 2.0 \text{ V}, I_{C} = 300 \text{ mA}$	100		
		PN3638	30		
		<b>PN3638A</b> V <sub>CE</sub> = 10 V, I <sub>C</sub> = 100 mA	20		
		V <sub>CE</sub> = 10 V, I <sub>C</sub> = 100 mA <b>PN3638</b>	20		
		PN3638A	80		
		V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1.0 mA <b>PN3638A</b>	100		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$	100	0.25	V
	Base Feether Octoreties Wellson	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$ $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$	0.8	1.1 2.0	V
SMALL S	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz <b>PN3638</b> <b>PN3638</b>		20	pF
Cib	Input Capacitance	<b>PN3638A</b> V <sub>BE</sub> = 0.5 V, f = 1.0 MHz		10	pF
Olb	mpar capacitarios				
		PN3638		65 25	pF pF
hfe	Small-Signal Current Gain	PN3638A		65 25	pF pF
h <sub>fe</sub>	Small-Signal Current Gain	PN3638A Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638	1.0		
h <sub>fe</sub>	Small-Signal Current Gain	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A	1.0 1.5		
h <sub>fe</sub>	Small-Signal Current Gain	PN3638A Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638			
h <sub>fe</sub>		PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A	1.5	25	pF
	Input Impedance	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V,	1.5 25	25	pF
h <sub>ie</sub>	Input Impedance Output Admittance	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz	1.5 25	2.0 1.2	pF kΩ μmhos
h <sub>ie</sub>	Input Impedance	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V,	1.5 25	25	kΩ μmhos
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub>	Input Impedance Output Admittance Voltage Feedback Ratio	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638A	1.5 25	2.0 1.2 2.6	pF kΩ μmhos
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub> SWITCHI	Input Impedance Output Admittance Voltage Feedback Ratio  NG CHARACTERISTICS	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V, f = 1.0 kHz PN3638 I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V, f = 1.0 kHz PN3638A  I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V, f = 1.0 kHz PN3638 PN3638A	1.5 25 100	2.0 1.2 2.6	kΩ μmhos x10 <sup>-4</sup>
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub> SWITCHI	Input Impedance Output Admittance Voltage Feedback Ratio  NG CHARACTERISTICS Turn-on Time	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  VcC = 10 V, Ic = 300 mA,	1.5 25 100	2.0 1.2 2.6	kΩ μmhos x10 <sup>-4</sup> x10 <sup>-4</sup>
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub> SWITCHI	Input Impedance Output Admittance Voltage Feedback Ratio  NG CHARACTERISTICS Turn-on Time Delay Time	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V, f = 1.0 kHz PN3638 I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V, f = 1.0 kHz PN3638A  I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V, f = 1.0 kHz PN3638 PN3638A	1.5 25 100 75 20	2.0 1.2 2.6	kΩ μmhos x10 <sup>-4</sup> ns
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub> SWITCHI ton td	Input Impedance Output Admittance Voltage Feedback Ratio  NG CHARACTERISTICS Turn-on Time Delay Time Rise Time	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  VcC = 10 V, Ic = 300 mA, IB1 = 30 mA	75 20 70	2.0 1.2 2.6	kΩ μmhos x10 <sup>-4</sup> x10 <sup>-4</sup>
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub> SWITCHI ton td	Input Impedance Output Admittance Voltage Feedback Ratio  NG CHARACTERISTICS Turn-on Time Delay Time Rise Time Turn-off Time	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638A  VcC = 10 V, Ic = 300 mA, IB1 = 30 mA  Vcc = 10 V, Ic = 300 mA	75 20 70	2.0 1.2 2.6	kΩ μmhos x10 <sup>-4</sup> x10 <sup>-4</sup> ns ns ns
h <sub>ie</sub> h <sub>oe</sub> h <sub>re</sub> SWITCHI ton	Input Impedance Output Admittance Voltage Feedback Ratio  NG CHARACTERISTICS Turn-on Time Delay Time Rise Time	PN3638A  Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  Ic = 10 mA, VcE = 10 V, f = 1.0 kHz PN3638 PN3638A  VcC = 10 V, Ic = 300 mA, IB1 = 30 mA	75 20 70	2.0 1.2 2.6	kΩ μmhos x10 <sup>-4</sup> x10 <sup>-4</sup>

#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

#### TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

#### Machine Option "A" (H)

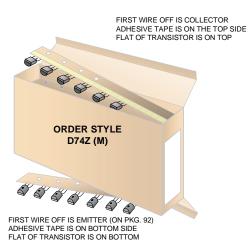


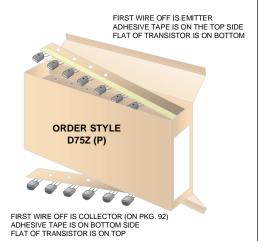
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0



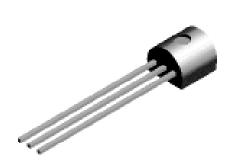


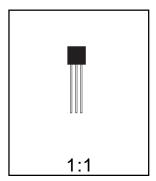


#### **TO-92 Package Dimensions**



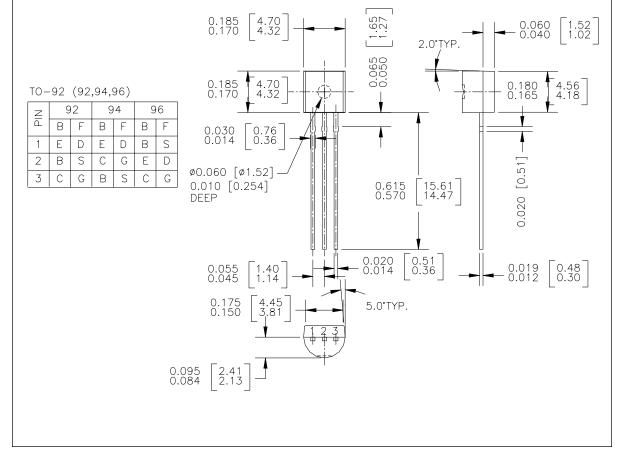
# TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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DOME™ ISOPLANAR™ Quiet Series™

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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